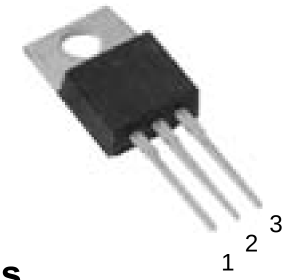
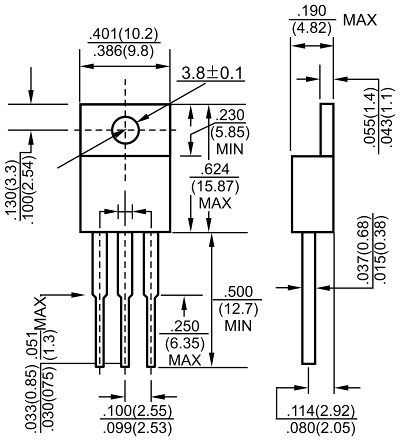
2SC2073(NPN)

TO-220 Transistor

TO-220



1. BASE
2. COLLECTOR
3. EMITTER



Dimensions in inches and (millimeters)

Features

- ✧ Wide safe Operating Area.
- ✧ Complementary to 2SA940

MAXIMUM RATINGS (T_A=25℃ unless otherwise noted)

Symbol	Paramenter	Value	Units
V_{CBO}	Collector-Base Voltage	150	V
V_{CEO}	Collector-Emitter Voltage	150	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current -Continuous	1.5	A
P_C	Collector Power Dissipation	1.5	W
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55-150	℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C =100μA, I_E=0	150			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C =1mA, I_B=0	150			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=100μA, I_C=0	5			V
Collector cut-off current	I_{CBO}	V_{CB}=120V, I_E=0			10	μA
Emitter cut-off current	I_{EBO}	V_{EB}=5V, I_C=0			10	μA
DC current gain	h_{FE}	V_{CE}=10V, I_C=0.5A	40		140	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=0.5A, I_B=50mA			1.5	V
Base-emitter voltage	V_{BE}	V_{CE}=10V, I_C=0.5A	0.65		0.85	V
Transition frequency	f_T	V_{CE}=10V, I_C=0.5A		4		MHz
Collector output capacitance	C_{ob}	V_{CB}=10V, I_E=0, f=1MHz		35		pF

Typical Characteristics